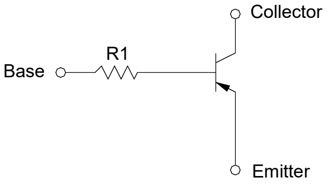
RA110S…RA114S

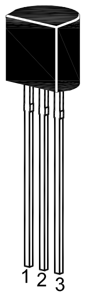
PNP Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process





1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 5 V, $-I_C$ = 1 mA		h_{FE}	120	-	-	-
Collector Base Cutoff Current at $-V_{CB}$ = 50 V		$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V		$-I_{EBO}$	-	-	100	nA
Collector Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 0.5 mA		$-V_{CE(sat)}$	-	-	0.3	V
Transition Frequency at $-V_{CE}$ = 10 V, $-I_C$ = 5 mA		f_T	-	250	-	MHz
Input Resistor	RA110S	R_1	-	4.7	-	KΩ
	RA111S		-	10	-	
	RA112S		-	100	-	
	RA113S		-	22	-	
	RA114S		-	47	-	

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